

Silicon NPN Power Transistors

2SC515

DESCRIPTION

- With TO-66 package
- High breakdown voltage

APPLICATIONS

- For use in line-operated color TV chroma output circuits and sound output circuits

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

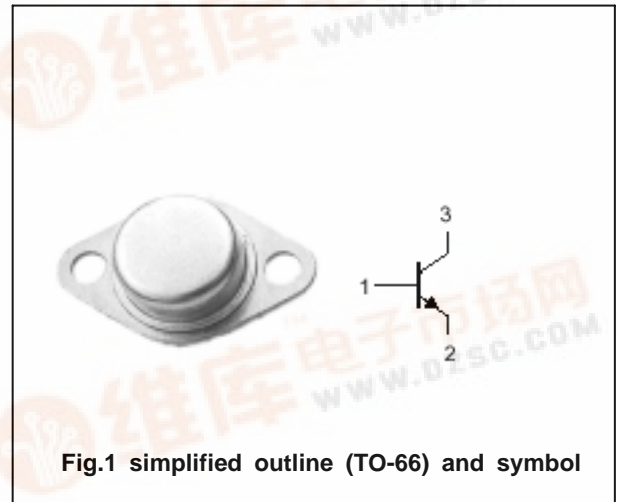


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta= )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	300	V
$V_{CEO}$	Collector-emitter voltage	Open base	300	V
$V_{EBO}$	Emitter-base voltage	Open collector	7	V
$I_C$	Collector current		0.1	A
$P_D$	Total power dissipation	$T_C=25$	6	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =1mA; I <sub>B</sub> =0	300			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =10 μA; I <sub>E</sub> =0	300			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =10 μA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =50mA; I <sub>B</sub> =5mA			2.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =200V; I <sub>E</sub> =0			100	nA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			100	nA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =50mA; V <sub>CE</sub> =10V	30		150	

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PACKAGE OUTLINE

